#### 研究论文

热处理温度对铬掺杂二氧化钛表面结构和性质的影响

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摘要 采用溶胶-凝胶法制备了铬掺杂二氧化钛(Cr-TiO<sub>2</sub>),并对经过不同温度烧结的Cr-TiO<sub>2</sub>的结构、吸收光谱及样品中铬的氧化态等进行了表征. 实验结果表明,在不高于723 K的温度烧结后,铬以Cr<sup>3</sup> +的氧化物和Cr<sup>6+</sup>的铬酸盐或重铬酸盐的形式存在于TiO<sub>2</sub>表面. 随着热处理温度的提高,Cr<sup>6+</sup>的含量逐渐增多. Cr-TiO<sub>2</sub>在可见区400~550 nm的吸收带是由Cr<sup>3+</sup>的 $^4$ A<sub>2</sub>→ $^4$ T<sub>1</sub>跃迁和O→Cr<sup>6+</sup>的 $^4$ 的 $^4$ L<sub>1</sub>→2e电荷转移等引起的,620~800 nm的吸收则是Cr<sup>3+</sup>的 $^4$ A<sub>2</sub>→ $^4$ T<sub>2</sub>跃迁的结果. 前者随着烧结温度的升高而增强,后者则随着温度升高而下降. 关键词 <u>半导体</u><u>掺杂</u>二氧化钛 <u>格</u>可见光吸收</u>分类号

# **Effect of Annealing Temperature on the Surface Structure and Properties of Chromium Doped Titania**

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**Abstract** Chromium doped titanium dioxide  $\operatorname{Cr-TiO}_2$  was prepared by the sol-gel method. The effects of annealing temperature on the crystal structure, oxidation states of chromium, and UV-vis absorption properties of  $\operatorname{Cr-TiO}_2$  were investigated in details. Experiment results showed that chromium mainly existed on  $\operatorname{TiO}_2$  surface as  $\operatorname{Cr}_2\operatorname{O}_3$  and chromate or dichromate of  $\operatorname{Cr}^{6+}$  in  $\operatorname{Cr-TiO}_2$  annealed at temperature no higher than 723 K. The content of  $\operatorname{Cr}^{6+}$  was increased with the increase of temperature. The visible light absorption of  $\operatorname{Cr-TiO}_2$  within  $400 \sim 550$  nm should be attributed to the  ${}^4\operatorname{A}_2 \rightarrow {}^4\operatorname{T}_1$  transition of  $\operatorname{Cr}^{3+}$  and the  $\operatorname{O} \rightarrow \operatorname{Cr}^{6+}$  charge transfer ( $\operatorname{It}_1 \rightarrow \operatorname{2e}$ ). The absorption within  $\operatorname{620} \sim 800$  nm was due to the  ${}^4\operatorname{A}_2 \rightarrow {}^4\operatorname{T}_2$  transition of  $\operatorname{Cr}^{3+}$ . The former was strengthened with the increase of annealing temperature, whereas the latter was weakened.

Key words semiconductor doping titanium dioxide chromium visible light absorption

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